

Claims 4-7, 9, 13-15, and 17-36 are active in the present application. Claims 6, 7, 9, 15, 17-22 and 25-26 have been amended to remove multiple dependencies. Claims 27-36 are new claims. Support for the new claims is found in the specification on page 4, line 19 through page 8, line 15 and in the original claims. No new matter is believed to have been added by this amendment. An action on the merits and allowance of claims is solicited.

Respectfully submitted,

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IN THE TITLE

Please replace the title on page 1, lines 3-5 with the following title.

--CARBON-CONTAINING ALUMINIUM NITRIDE SINTERED COMPACT
AND CERAMIC SUBSTRATE FOR USE IN EQUIPMENT
FOR MANUFACTURING OR INSPECTING SEMICONDUCTOR--

IN THE CLAIMS

Please amend the claims as follows:

--6. (Amended) The carbon-containing aluminum nitride sintered body according to claim 4 [or 5],

which comprises both of crystalline carbon and amorphous carbon.

7. (Amended) The carbon-containing aluminum nitride sintered body according to [any of claims 4 to 6] claim 4,

which comprises said carbon in a total amount of 200 to 5000 ppm.

9. (Amended) The carbon-containing aluminum nitride sintered body according to [any of claims 4 to 7] claim 4,

wherein its brightness defined in JIS Z 8721 is N4 or less.

15. (Amended) The ceramic substrate for the semiconductor-producing/examining device according to claim 13 [or 14],

wherein the content of said carbon is from 200 to 5000 ppm.

17. (Amended) The ceramic substrate for the semiconductor-producing/examining device according to [any of claims 13 to 15] claim 13,

wherein its brightness defined in JIS Z 8721 is N4 or less.

18. (Amended) The ceramic substrate for the semiconductor-producing/examining device according to [any of claims 13 to 15, and 17] claim 13,

wherein:

said conductor is an electrostatic electrode; and

said ceramic substrate functions as an electrostatic chuck.

19. (Amended) The ceramic substrate for the semiconductor-producing/examining device according to [any of claims 13 to 15, and 17] claim 13,

wherein:

said conductor is a resistance heating element; and

said ceramic substrate functions as a hot plate.

20. (Amended) The ceramic substrate for the semiconductor-producing/examining device according to [any of claims 13 to 15, and 17] claim 13,

wherein:

said conductor is formed: on a surface of the ceramic substrate; and inside the ceramic substrate;

said inside conductor is at least one of a guard electrode and a ground electrode; and

said ceramic substrate functions as a wafer prober.

21. (Amended) A carbon-containing aluminum nitride sintered body according to [any of claims 4 to 7] claim 4,

wherein:

said matrix contains a sintering aid comprising at least one of an alkali metal oxide, an alkali earth metal oxide, and a rare earth oxide; and,
its brightness defined in JIS Z 8721 is N4 or less.

22. (Amended) The ceramic substrate for the semiconductor-producing/examining device according to [any of claims 13 to 15] claim 14,
wherein:

said ceramic substrate contains a sintering aid comprising at least one of an alkali metal oxide, an alkali earth metal oxide, and a rare earth oxide; and,
its brightness defined in JIS Z 8721 is N4 or less.

25. (Amended) The carbon-containing aluminum nitride sintered body according to claim 23 [or 24],

wherein the content of said carbon is from 200 to 5000 ppm.

26. (Amended) The carbon-containing aluminum nitride sintered body according to [any of claims 23 to 25] claim 23,

wherein said matrix contains a sintering aid comprising at least one of an alkali metal oxide, an alkali earth metal oxide, and a rare earth oxide.--

Claims 27-36 (New).